

electrical energy from heat sources (stoves and the like) and whose particular spectrum is, mainly, infrared.

7. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because the photovoltaic converter is assembled to an optical concentrator by means of silicone rubbers, epoxies, resins or something similar.

8. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized by carrying out the conversion of light channeled by optical fiber and coming from a laser into electricity for high-risk environments such as the powering of sensors and electronics in applications such as mines, high-tension grids, the chemical and petrochemical industries, nuclear power plants, airplanes, rockets, satellites, biomedicine, etc.

9. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because its encapsulation is carried out by means of optoelectronic techniques such as: a) fixing the converter by means of its rear contact to a support using epoxy or solder, and b) connection of the front contact by means of wire bonding, pick and place, flip-chip, multichip-module or something similar.

10. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because it consists of a single semiconductor junction.

11. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because it consists of several semiconductor junctions.

12. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized for possessing a monolithic connection in series in order to increase the output voltage.

13. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because it consists of a single semiconductor junction.

14. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because it consists of several semiconductor junctions.

15. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized for possessing a monolithic connection in series in order to increase the output voltage.

16. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because its encapsulation is carried out by means of optoelectronic techniques such as: a) fixing the converter by means of its rear contact to a support using epoxy or solder, and b) connection of the frontal contact by means of wire bonding, pick and place, flip-chip, multichip-module or something similar.

17. (once amended) High efficiency photovoltaic converter for high luminous intensities manufactured using optoelectronic technology according to claim 1 characterized because the design parameters (semiconductor structure of III-V compounds, ohmic contacts, geometry, metal grid and antireflection layers) are calculated by means of a multivariable optimization.

REMARKS

The above amendments are made to correct multiple dependency in the claims. No new matter is contained in the amendment.

Please charge any fee deficiency or credit any overpayment to Deposit Account No. 50-1088.

Respectfully submitted,

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